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Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	120MHz
Connectivity	CANbus, Ethernet, I ² C, IrDA, LINbus, Memory Card, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LCD, POR, PWM, WDT
Number of I/O	114
Program Memory Size	768KB (768K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	132K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	144-LQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f207zft6

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Table 8. STM32F20x pin and ball definitions (continued)

Pins						Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Note	Alternate functions	Additional functions
LQFP64	WLCSP64+2	LQFP100	LQFP144	LQFP176	UFBGA176						
13	-	22	33	39	R1	V _{DDA}	S	-	-	-	-
14	E7	23	34	40	N3	PA0-WKUP (PA0)	I/O	FT	(4)(5)	USART2_CTS, UART4_TX, ETH_MII_CRS, TIM2_CH1_ETR, TIM5_CH1, TIM8_ETR, EVENTOUT	ADC123_IN0, WKUP
15	H8	24	35	41	N2	PA1	I/O	FT	(4)	USART2_RTS, UART4_RX, ETH_RMII_REF_CLK, ETH_MII_RX_CLK, TIM5_CH2, TIM2_CH2, EVENTOUT	ADC123_IN1
16	J9	25	36	42	P2	PA2	I/O	FT	(4)	USART2_TX, TIM5_CH3, TIM9_CH1, TIM2_CH3, ETH_MDIO, EVENTOUT	ADC123_IN2
-	-	-	-	43	F4	PH2	I/O	FT	-	ETH_MII_CRS, EVENTOUT	-
-	-	-	-	44	G4	PH3	I/O	FT	-	ETH_MII_COL, EVENTOUT	-
-	-	-	-	45	H4	PH4	I/O	FT	-	I2C2_SCL, OTG_HS_ULPI_NXT, EVENTOUT	-
-	-	-	-	46	J4	PH5	I/O	FT	-	I2C2_SDA, EVENTOUT	-
17	G7	26	37	47	R2	PA3	I/O	FT	(4)	USART2_RX, TIM5_CH4, TIM9_CH2, TIM2_CH4, OTG_HS_ULPI_D0, ETH_MII_COL, EVENTOUT	ADC123_IN3
18	F1	27	38	48	-	V _{SS}	S	-	-	-	-
	H7				L4	REGOFF	I/O	-	-	-	-
19	E1	28	39	49	K4	V _{DD}	S	-	-	-	-
20	J8	29	40	50	N4	PA4	I/O	TTa	(4)	SPI1_NSS, SPI3_NSS, USART2_CK, DCMI_HSYNC, OTG_HS_SOF, I2S3_WS, EVENTOUT	ADC12_IN4, DAC_OUT1
21	H6	30	41	51	P4	PA5	I/O	TTa	(4)	SPI1_SCK, OTG_HS_ULPI_CK, TIM2_CH1_ETR, TIM8_CH1N, EVENTOUT	ADC12_IN5, DAC_OUT2

Table 8. STM32F20x pin and ball definitions (continued)

Pins						Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Note	Alternate functions	Additional functions
LQFP64	WLCSP64+2	LQFP100	LQFP144	LQFP176	UFBGA176						
-	-	38	58	68	R8	PE7	I/O	FT	-	FSMC_D4,TIM1_ETR, EVENTOUT	-
-	-	39	59	69	P8	PE8	I/O	FT	-	FSMC_D5,TIM1_CH1N, EVENTOUT	-
-	-	40	60	70	P9	PE9	I/O	FT	-	FSMC_D6,TIM1_CH1, EVENTOUT	-
-	-	-	61	71	M9	V _{SS}	S		-	-	-
-	-	-	62	72	N9	V _{DD}	S		-	-	-
-	-	41	63	73	R9	PE10	I/O	FT	-	FSMC_D7,TIM1_CH2N, EVENTOUT	-
-	-	42	64	74	P10	PE11	I/O	FT	-	FSMC_D8,TIM1_CH2, EVENTOUT	-
-	-	43	65	75	R10	PE12	I/O	FT	-	FSMC_D9,TIM1_CH3N, EVENTOUT	-
-	-	44	66	76	N11	PE13	I/O	FT	-	FSMC_D10,TIM1_CH3, EVENTOUT	-
-	-	45	67	77	P11	PE14	I/O	FT	-	FSMC_D11,TIM1_CH4, EVENTOUT	-
-	-	46	68	78	R11	PE15	I/O	FT	-	FSMC_D12,TIM1_BKIN, EVENTOUT	-
29	H3	47	69	79	R12	PB10	I/O	FT	-	SPI2_SCK, I2S2_SCK, I2C2_SCL,USART3_TX,OT G_HS_ULPI_D3,ETH_MII_R X_ER,TIM2_CH3, EVENTOUT	-
30	J2	48	70	80	R13	PB11	I/O	FT	-	I2C2_SDA, USART3_RX, OTG_HS_ULPI_D4, ETH_RMII_TX_EN, ETH_MII_TX_EN, TIM2_CH4, EVENTOUT	-
31	J3	49	71	81	M10	V _{CAP_1}	S		-	-	-
32	-	50	72	82	N10	V _{DD}	S		-	-	-
-	-	-	-	83	M11	PH6	I/O	FT	-	I2C2_SMBA, TIM12_CH1, ETH_MII_RXD2, EVENTOUT	-

Typical and maximum current consumption

The MCU is placed under the following conditions:

- At startup, all I/O pins are configured as analog inputs by firmware.
- All peripherals are disabled except if it is explicitly mentioned.
- The Flash memory access time is adjusted to f_{HCLK} frequency (0 wait state from 0 to 30 MHz, 1 wait state from 30 to 60 MHz, 2 wait states from 60 to 90 MHz and 3 wait states from 90 to 120 MHz).
- When the peripherals are enabled HCLK is the system clock, $f_{PCLK1} = f_{HCLK}/4$, and $f_{PCLK2} = f_{HCLK}/2$, except is explicitly mentioned.
- The maximum values are obtained for $V_{DD} = 3.6$ V and maximum ambient temperature (T_A), and the typical values for $T_A = 25$ °C and $V_{DD} = 3.3$ V unless otherwise specified.

Table 20. Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator enabled) or RAM ⁽¹⁾

Symbol	Parameter	Conditions	f_{HCLK}	Typ	Max ⁽²⁾		Unit
				$T_A = 25$ °C	$T_A = 85$ °C	$T_A = 105$ °C	
I_{DD}	Supply current in Run mode	External clock ⁽³⁾ , all peripherals enabled ⁽⁴⁾	120 MHz	49	63	72	mA
			90 MHz	38	51	61	
			60 MHz	26	39	49	
			30 MHz	14	27	37	
			25 MHz	11	24	34	
			16 MHz ⁽⁵⁾	8	21	30	
			8 MHz	5	17	27	
			4 MHz	3	16	26	
			2 MHz	2	15	25	
		External clock ⁽³⁾ , all peripherals disabled	120 MHz	21	34	44	
			90 MHz	17	30	40	
			60 MHz	12	25	35	
			30 MHz	7	20	30	
			25 MHz	5	18	28	
			16 MHz ⁽⁵⁾	4.0	17.0	27.0	
			8 MHz	2.5	15.5	25.5	
			4 MHz	2.0	14.7	24.8	
			2 MHz	1.6	14.5	24.6	

1. Code and data processing running from SRAM1 using boot pins.

2. Guaranteed by characterization, tested in production at V_{DD} max and f_{HCLK} max with peripherals enabled.

3. External clock is 4 MHz and PLL is on when $f_{HCLK} > 25$ MHz.

4. When the ADC is on (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.6 mA per ADC for the analog part.

5. In this case HCLK = system clock/2.

Figure 25. Typical current consumption vs. temperature, Run mode, code with data processing running from Flash, ART accelerator OFF, peripherals ON

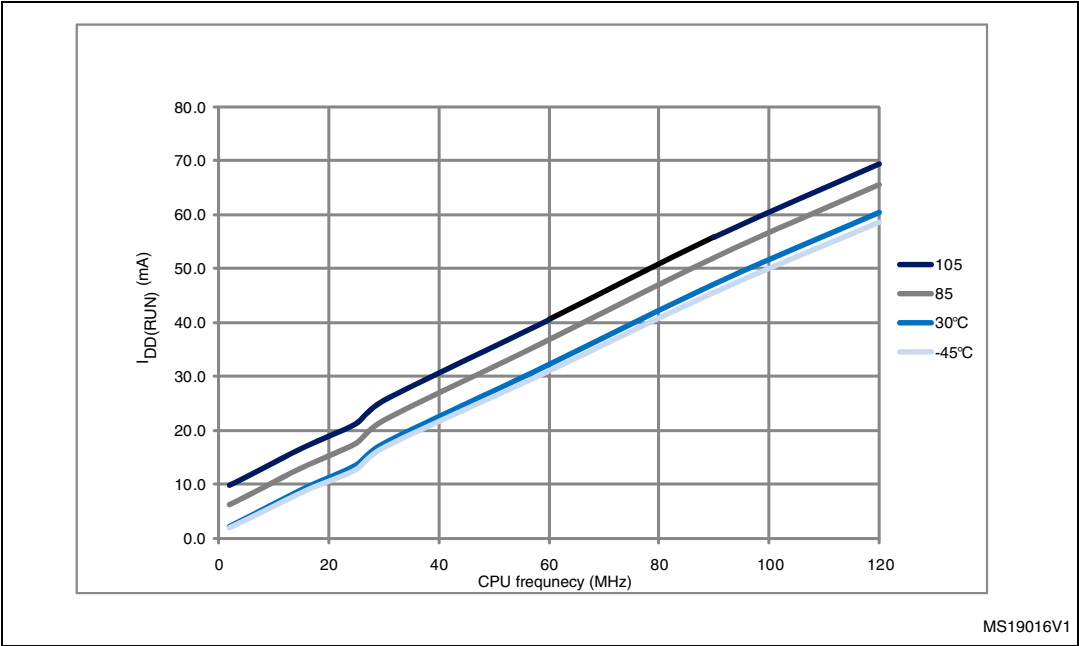
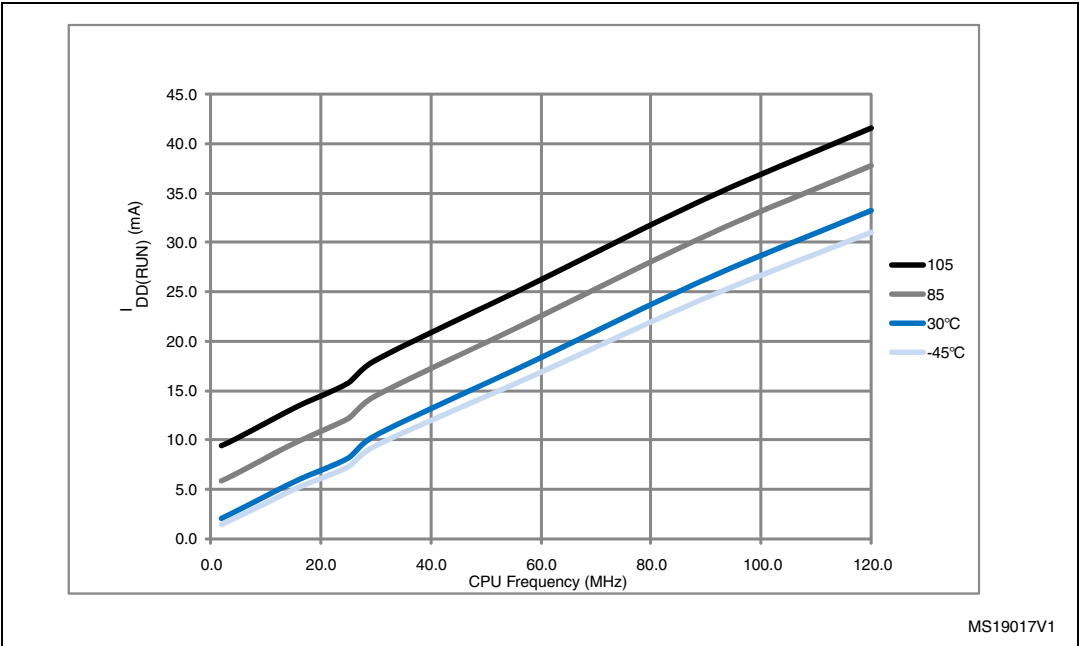


Figure 26. Typical current consumption vs. temperature, Run mode, code with data processing running from Flash, ART accelerator OFF, peripherals OFF



6.3.8 External clock source characteristics

High-speed external user clock generated from an external source

The characteristics given in [Table 28](#) result from tests performed using an high-speed external clock source, and under ambient temperature and supply voltage conditions summarized in [Table 14](#).

Table 28. High-speed external user clock characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSE_ext}	External user clock source frequency ⁽¹⁾	-	1	-	26	MHz
V_{HSEH}	OSC_IN input pin high level voltage		$0.7V_{DD}$	-	V_{DD}	V
V_{HSEL}	OSC_IN input pin low level voltage		V_{SS}	-	$0.3V_{DD}$	
$t_{w(HSE)}$ $t_{f(HSE)}$	OSC_IN high or low time ⁽¹⁾		5	-	-	ns
$t_{r(HSE)}$ $t_{f(HSE)}$	OSC_IN rise or fall time ⁽¹⁾		-	-	20	
$C_{in(HSE)}$	OSC_IN input capacitance ⁽¹⁾	-	-	5	-	pF
$DuCy_{(HSE)}$	Duty cycle	-	45	-	55	%
I_L	OSC_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	± 1	μA

1. Guaranteed by design, not tested in production.

Low-speed external user clock generated from an external source

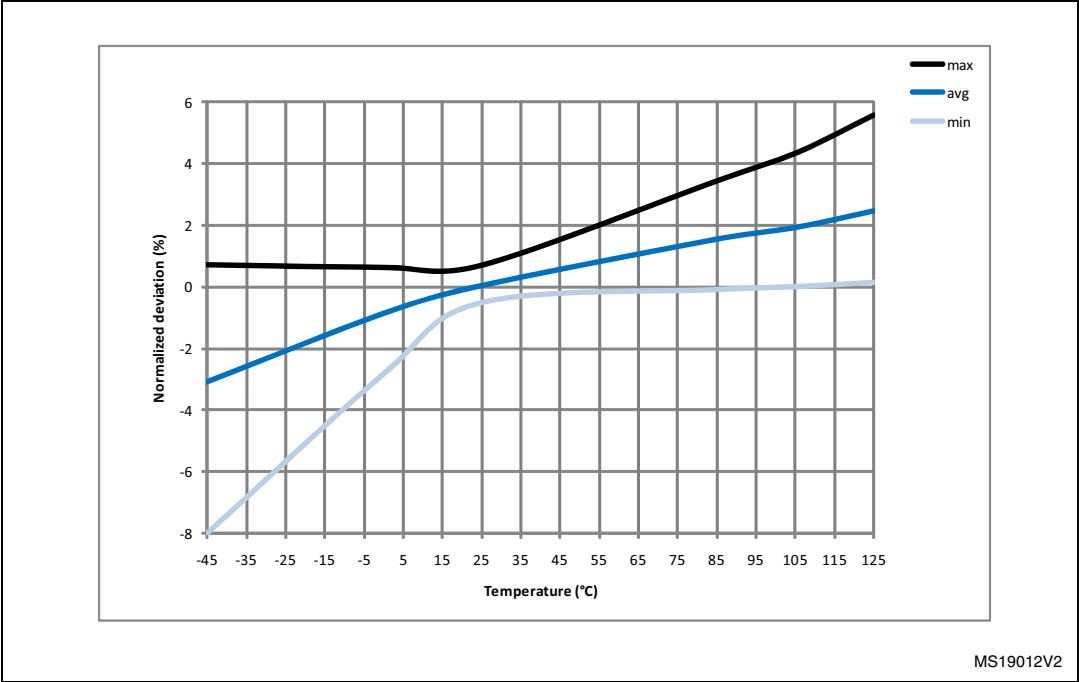
The characteristics given in [Table 29](#) result from tests performed using an low-speed external clock source, and under ambient temperature and supply voltage conditions summarized in [Table 14](#).

Table 29. Low-speed external user clock characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{LSE_ext}	User External clock source frequency ⁽¹⁾	-	-	32.768	1000	kHz
V_{LSEH}	OSC32_IN input pin high level voltage		$0.7V_{DD}$	-	V_{DD}	V
V_{LSEL}	OSC32_IN input pin low level voltage		V_{SS}	-	$0.3V_{DD}$	
$t_{w(LSE)}$ $t_{f(LSE)}$	OSC32_IN high or low time ⁽¹⁾		450	-	-	ns
$t_{r(LSE)}$ $t_{f(LSE)}$	OSC32_IN rise or fall time ⁽¹⁾		-	-	50	
$C_{in(LSE)}$	OSC32_IN input capacitance ⁽¹⁾	-	-	5	-	pF
$DuCy_{(LSE)}$	Duty cycle	-	30	-	70	%
I_L	OSC32_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	± 1	μA

1. Guaranteed by design, not tested in production.

Figure 34. ACC_{HSI} versus temperature



Low-speed internal (LSI) RC oscillator

Table 33. LSI oscillator characteristics ⁽¹⁾

Symbol	Parameter	Min	Typ	Max	Unit
$f_{LSI}^{(2)}$	Frequency	17	32	47	kHz
$t_{su(LSI)}^{(3)}$	LSI oscillator startup time	-	15	40	μs
$I_{DD(LSI)}^{(3)}$	LSI oscillator power consumption	-	0.4	0.6	μA

- $V_{DD} = 3 V$, $T_A = -40$ to $105^\circ C$ unless otherwise specified.
- Guaranteed by characterization results, not tested in production.
- Guaranteed by design, not tested in production.

6.3.11 PLL spread spectrum clock generation (SSCG) characteristics

The spread spectrum clock generation (SSCG) feature allows to reduce electromagnetic interferences (see [Table 42: EMI characteristics](#)). It is available only on the main PLL.

Table 36. SSCG parameters constraint

Symbol	Parameter	Min	Typ	Max ⁽¹⁾	Unit
f_{Mod}	Modulation frequency	-	-	10	KHz
md	Peak modulation depth	0.25	-	2	%
MODEPER * INCSTEP	-	-	-	$2^{15}-1$	-

1. Guaranteed by design, not tested in production.

Equation 1

The frequency modulation period (MODEPER) is given by the equation below:

$$MODEPER = \text{round}[f_{PLL_IN} / (4 \times f_{Mod})]$$

f_{PLL_IN} and f_{Mod} must be expressed in Hz.

As an example:

If $f_{PLL_IN} = 1$ MHz and $f_{MOD} = 1$ kHz, the modulation depth (MODEPER) is given by equation 1:

$$MODEPER = \text{round}[10^6 / (4 \times 10^3)] = 250$$

Equation 2

Equation 2 allows to calculate the increment step (INCSTEP):

$$INCSTEP = \text{round}[(2^{15} - 1) \times md \times PLLN] / (100 \times 5 \times MODEPER)$$

f_{VCO_OUT} must be expressed in MHz.

With a modulation depth (md) = ± 2 % (4 % peak to peak), and PLLN = 240 (in MHz):

$$INCSTEP = \text{round}[(2^{15} - 1) \times 2 \times 240] / (100 \times 5 \times 250) = 126md(\text{quantitized})\%$$

An amplitude quantization error may be generated because the linear modulation profile is obtained by taking the quantized values (rounded to the nearest integer) of MODEPER and INCSTEP. As a result, the achieved modulation depth is quantized. The percentage quantized modulation depth is given by the following formula:

$$md_{\text{quantized}}\% = (MODEPER \times INCSTEP \times 100 \times 5) / ((2^{15} - 1) \times PLLN)$$

As a result:

$$md_{\text{quantized}}\% = (250 \times 126 \times 100 \times 5) / ((2^{15} - 1) \times 240) = 2.0002\%(\text{peak})$$

Figure 36 and *Figure 37* show the main PLL output clock waveforms in center spread and down spread modes, where:

F_0 is $f_{\text{PLL_OUT}}$ nominal.

T_{mode} is the modulation period.

md is the modulation depth.

Figure 36. PLL output clock waveforms in center spread mode

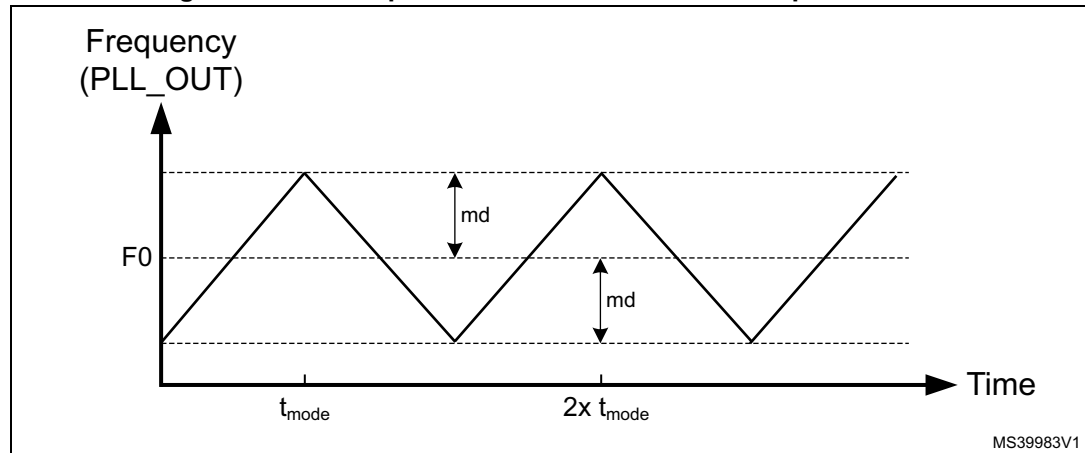
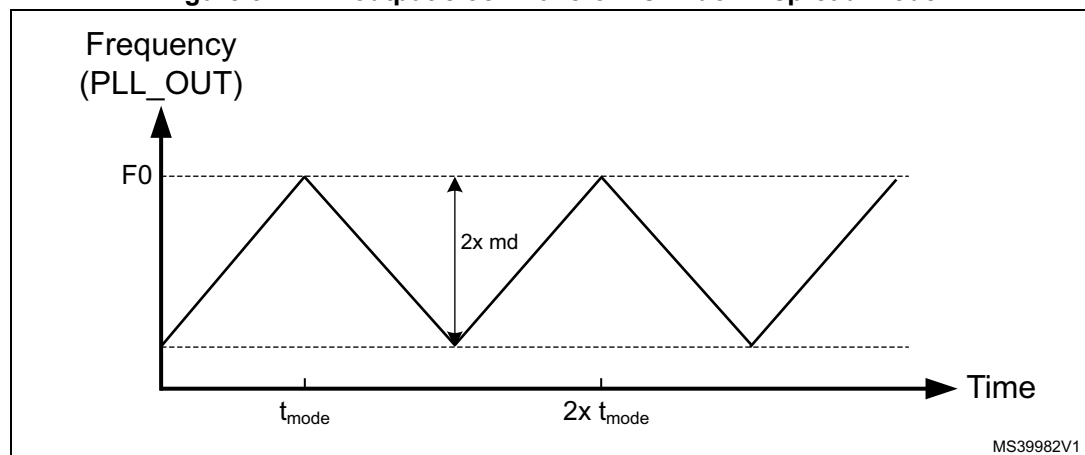


Figure 37. PLL output clock waveforms in down spread mode

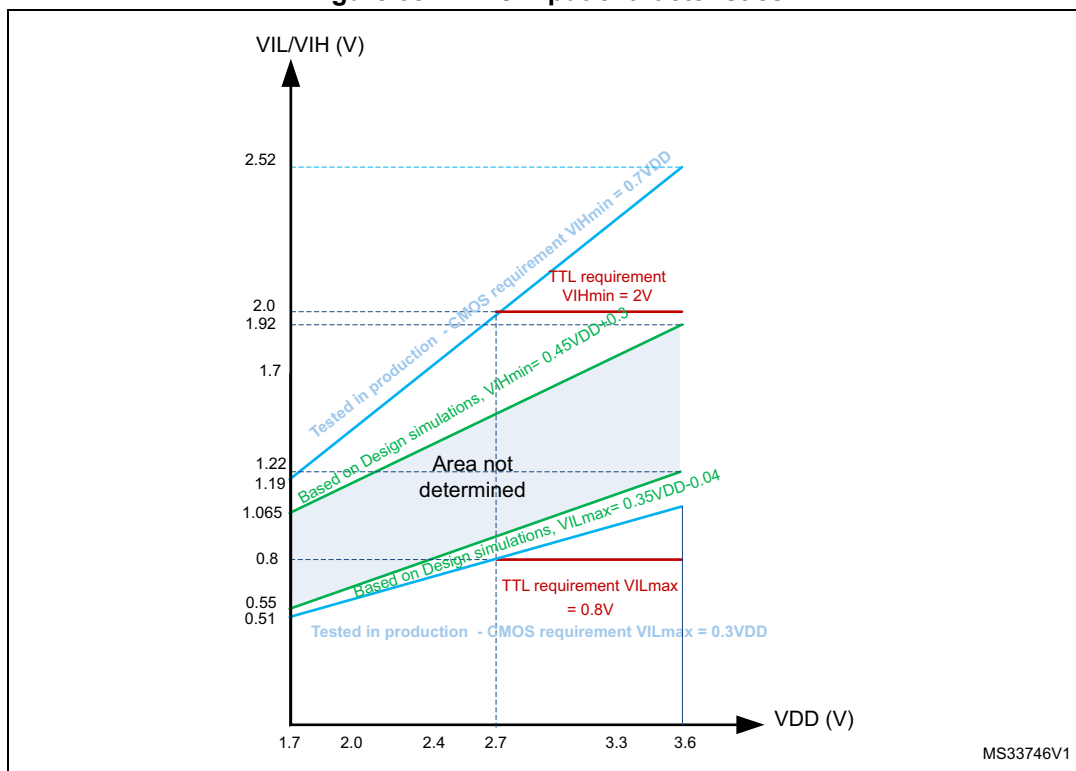


6.3.12 Memory characteristics

Flash memory

The characteristics are given at $T_A = -40$ to 105 °C unless otherwise specified.

Figure 38. FT I/O input characteristics



Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to ± 8 mA, and sink or source up to ± 20 mA (with a relaxed V_{OL}/V_{OH}) except PC13, PC14 and PC15 which can sink or source up to ± 3 mA. When using the PC13 to PC15 GPIOs in output mode, the speed should not exceed 2 MHz with a maximum load of 30 pF.

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in [Section 6.2](#):

- The sum of the currents sourced by all the I/Os on V_{DD} , plus the maximum Run consumption of the MCU sourced on V_{DD} , cannot exceed the absolute maximum rating I_{VDD} (see [Table 12](#)).
- The sum of the currents sunk by all the I/Os on V_{SS} plus the maximum Run consumption of the MCU sunk on V_{SS} cannot exceed the absolute maximum rating I_{VSS} (see [Table 12](#)).

Output voltage levels

Unless otherwise specified, the parameters given in [Table 47](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 14](#). All I/Os are CMOS and TTL compliant.

Table 51. Characteristics of TIMx connected to the APB2 domain⁽¹⁾

Symbol	Parameter	Conditions	Min	Max	Unit
t _{res(TIM)}	Timer resolution time	AHB/APB2 prescaler distinct from 1, f _{TIMxCLK} = 120 MHz	1	-	t _{TIMxCLK}
			8.3	-	ns
		AHB/APB2 prescaler = 1, f _{TIMxCLK} = 60 MHz	1	-	t _{TIMxCLK}
			16.7	-	ns
f _{EXT}	Timer external clock frequency on CH1 to CH4	f _{TIMxCLK} = 120 MHz APB2 = 60 MHz	0	f _{TIMxCLK} /2	MHz
			0	60	MHz
Res _{TIM}	Timer resolution		-	16	bit
t _{COUNTER}	16-bit counter clock period when internal clock is selected		1	65536	t _{TIMxCLK}
			0.0083	546	μs
t _{MAX_COUNT}	Maximum possible count		-	65536 × 65536	t _{TIMxCLK}
			-	35.79	s

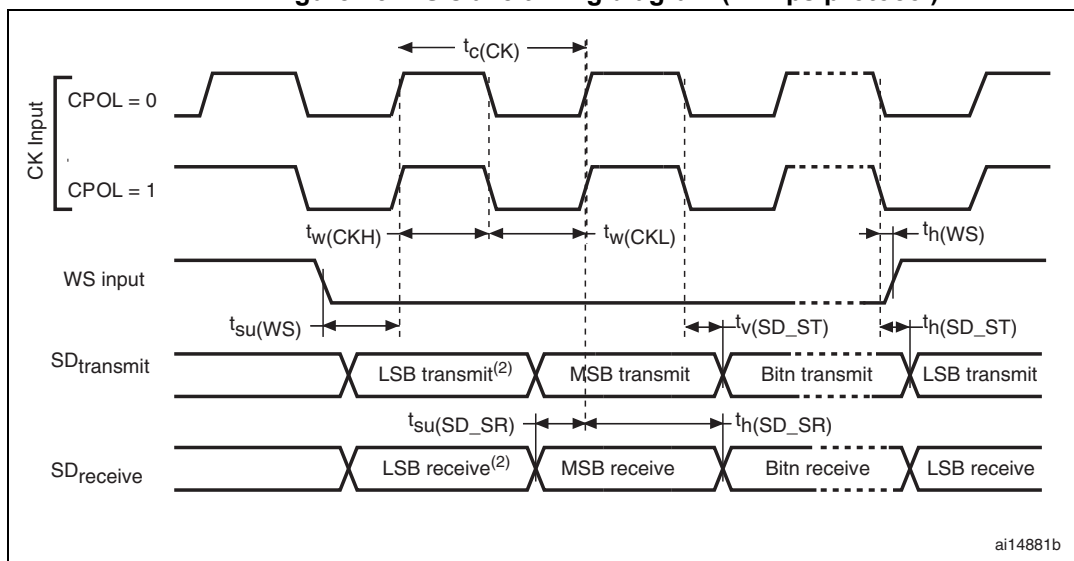
1. TIMx is used as a general term to refer to the TIM1, TIM8, TIM9, TIM10, and TIM11 timers.

6.3.19 Communications interfaces

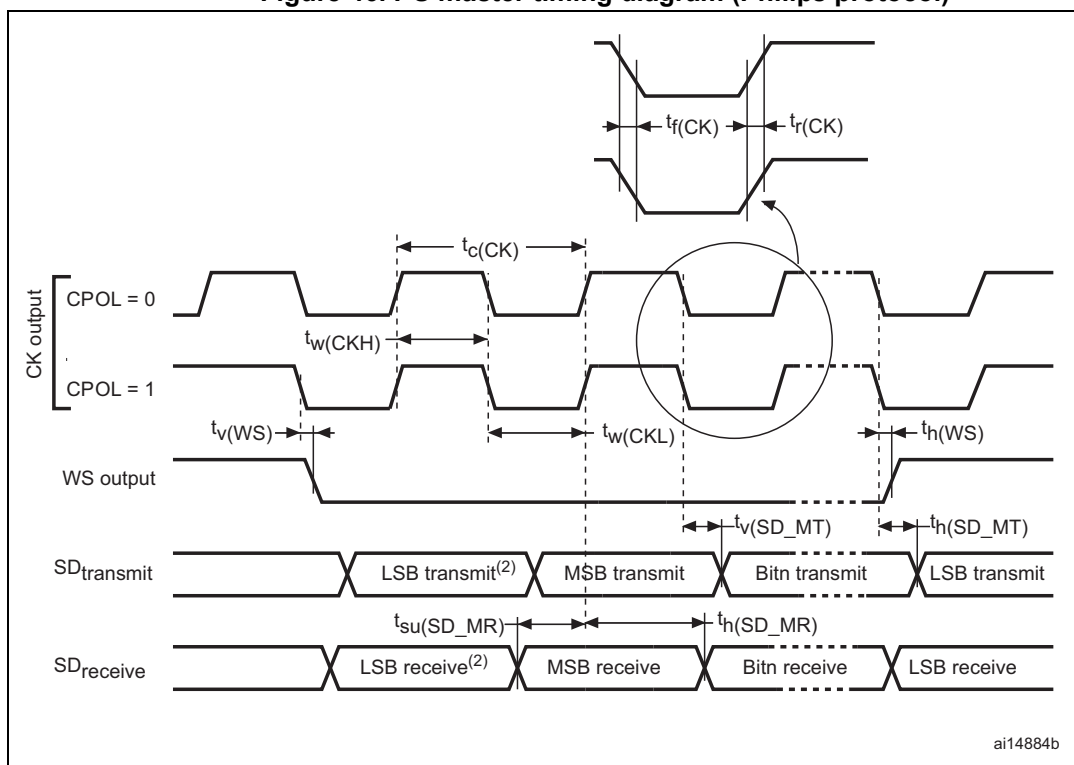
I²C interface characteristics

STM32F205xx and STM32F207xx I²C interface meets the requirements of the standard I²C communication protocol with the following restrictions: the I/O pins SDA and SCL are mapped to are not “true” open-drain. When configured as open-drain, the PMOS connected between the I/O pin and V_{DD} is disabled, but is still present.

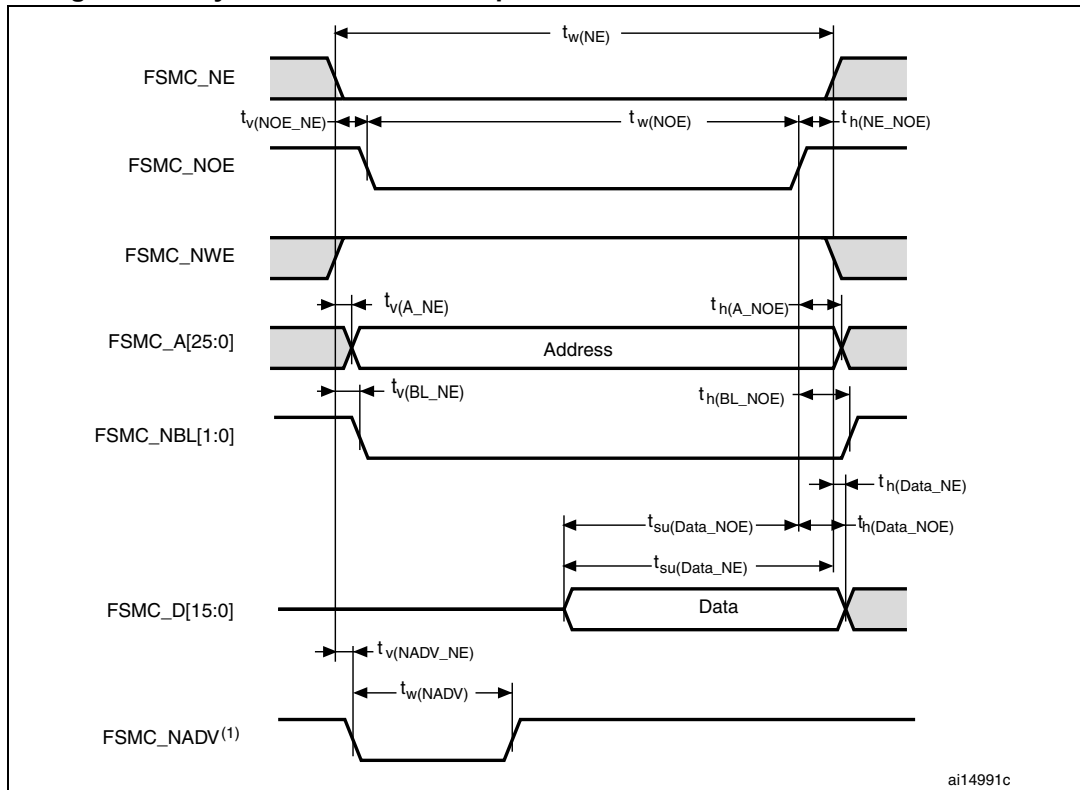
The I²C characteristics are described in [Table 52](#). Refer also to [Section 6.3.16: I/O port characteristics](#) for more details on the input/output alternate function characteristics (SDA and SCL).

Figure 45. I²S slave timing diagram (Philips protocol)⁽¹⁾

1. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

Figure 46. I²S master timing diagram (Philips protocol)⁽¹⁾

1. Guaranteed by characterization results, not tested in production.
2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

Figure 57. Asynchronous non-multiplexed SRAM/PSRAM/NOR read waveforms

1. Mode 2/B, C and D only. In Mode 1, FSMC_NADV is not used.

Table 72. Asynchronous non-multiplexed SRAM/PSRAM/NOR read timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FSMC_NE low time	$2T_{HCLK} - 0.5$	$2T_{HCLK} + 0.5$	ns
$t_{v(NOE_NE)}$	FSMC_NEx low to FSMC_NOE low	0.5	2.5	ns
$t_{w(NOE)}$	FSMC_NOE low time	$2T_{HCLK} - 1$	$2T_{HCLK} + 0.5$	ns
$t_{h(NE_NOE)}$	FSMC_NOE high to FSMC_NE high hold time	0	-	ns
$t_{v(A_NE)}$	FSMC_NEx low to FSMC_A valid	-	4	ns
$t_{h(A_NOE)}$	Address hold time after FSMC_NOE high	0	-	ns
$t_{v(BL_NE)}$	FSMC_NEx low to FSMC_BL valid	-	0.5	ns
$t_{h(BL_NOE)}$	FSMC_BL hold time after FSMC_NOE high	0	-	ns
$t_{su(Data_NE)}$	Data to FSMC_NEx high setup time	$T_{HCLK} + 0.5$	-	ns
$t_{su(Data_NOE)}$	Data to FSMC_NOEx high setup time	$T_{HCLK} + 2.5$	-	ns
$t_{h(Data_NOE)}$	Data hold time after FSMC_NOE high	0	-	ns
$t_{h(Data_NE)}$	Data hold time after FSMC_NEx high	0	-	ns
$t_{v(NADV_NE)}$	FSMC_NEx low to FSMC_NADV low	-	2.5	ns
$t_{w(NADV)}$	FSMC_NADV low time	-	$T_{HCLK} - 0.5$	ns

1. $C_L = 30$ pF.

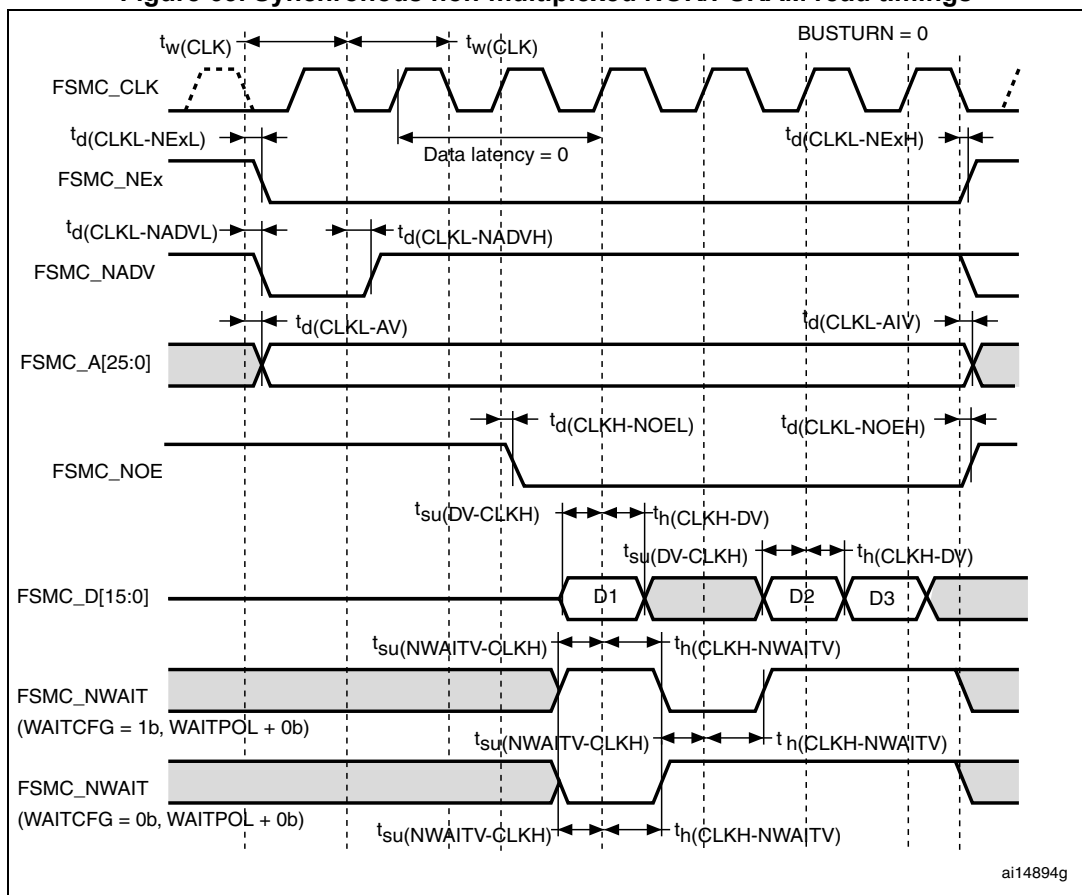
2. Guaranteed by characterization results, not tested in production.

Table 77. Synchronous multiplexed PSRAM write timings⁽¹⁾⁽²⁾ (continued)

Symbol	Parameter	Min	Max	Unit
$t_{d(CLKL-NWEL)}$	FSMC_CLK low to FSMC_NWE low	-	1	ns
$t_{d(CLKL-NWEH)}$	FSMC_CLK low to FSMC_NWE high	0	-	ns
$t_{d(CLKL-ADIV)}$	FSMC_CLK low to FSMC_AD[15:0] invalid	0	-	ns
$t_{d(CLKL-DATA)}$	FSMC_A/D[15:0] valid data after FSMC_CLK low	-	2	ns
$t_{d(CLKL-NBLH)}$	FSMC_CLK low to FSMC_NBL high	0.5	-	ns

1. $C_L = 30$ pF.

2. Guaranteed by characterization results, not tested in production.

Figure 63. Synchronous non-multiplexed NOR/PSRAM read timings**Table 78. Synchronous non-multiplexed NOR/PSRAM read timings⁽¹⁾⁽²⁾**

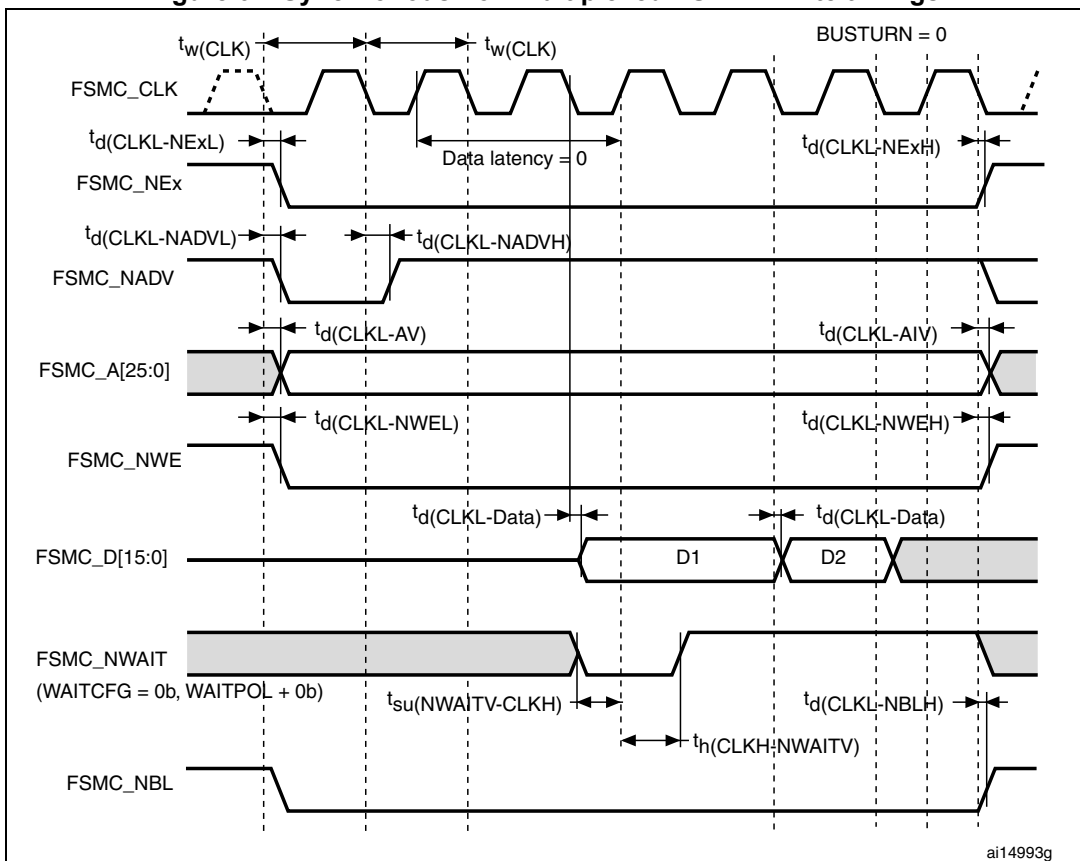
Symbol	Parameter	Min	Max	Unit
$t_w(CLK)$	FSMC_CLK period	$2T_{HCLK}$	-	ns
$t_{d(CLKL-NExL)}$	FSMC_CLK low to FSMC_NEx low ($x=0..2$)	-	0	ns
$t_{d(CLKL-NExH)}$	FSMC_CLK low to FSMC_NEx high ($x=0..2$)	1	-	ns
$t_{d(CLKL-NADV)}$	FSMC_CLK low to FSMC_NADV low	-	2.5	ns

Table 78. Synchronous non-multiplexed NOR/PSRAM read timings⁽¹⁾⁽²⁾ (continued)

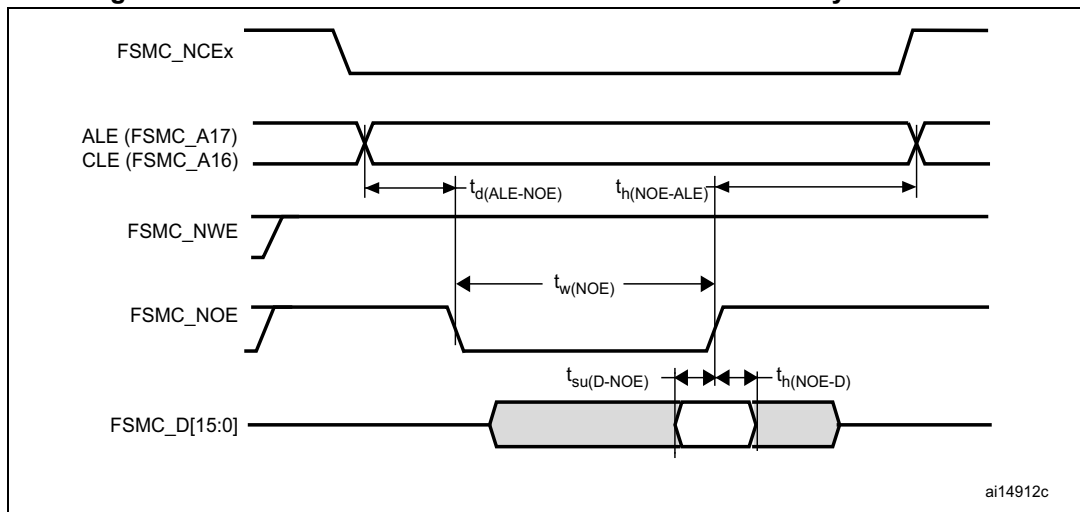
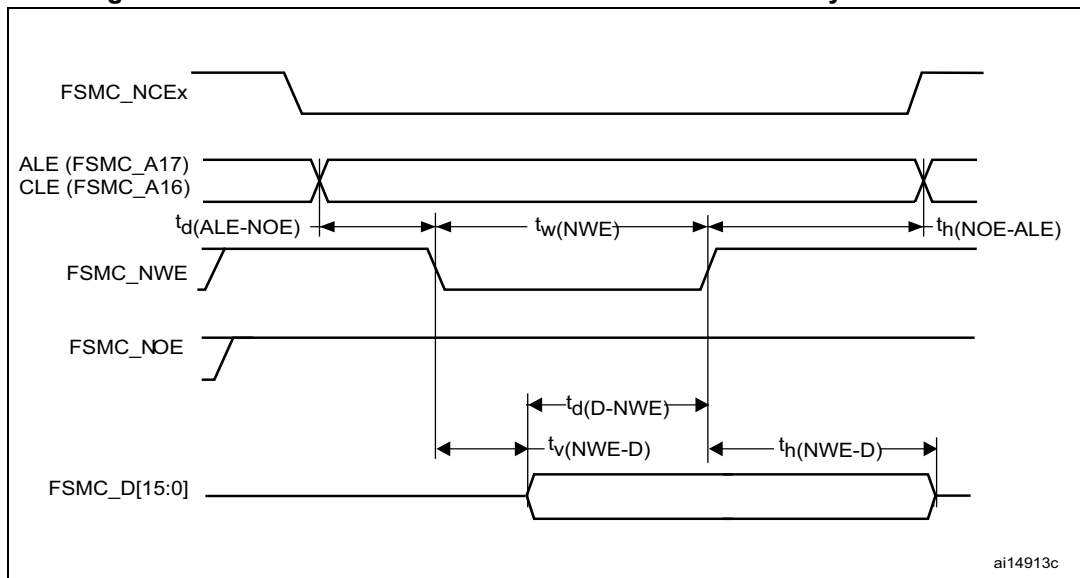
Symbol	Parameter	Min	Max	Unit
$t_{d(CLKL-NADVH)}$	FSMC_CLK low to FSMC_NADV high	4	-	ns
$t_{d(CLKL-AV)}$	FSMC_CLK low to FSMC_Ax valid (x=16...25)	-	0	ns
$t_{d(CLKL-AIV)}$	FSMC_CLK low to FSMC_Ax invalid (x=16...25)	3	-	ns
$t_{d(CLKH-NOEL)}$	FSMC_CLK high to FSMC_NOE low	-	1	ns
$t_{d(CLKL-NOEH)}$	FSMC_CLK low to FSMC_NOE high	1.5	-	ns
$t_{su(DV-CLKH)}$	FSMC_D[15:0] valid data before FSMC_CLK high	8	-	ns
$t_h(CLKH-DV)$	FSMC_D[15:0] valid data after FSMC_CLK high	0	-	ns

1. $C_L = 30$ pF.

2. Guaranteed by characterization results, not tested in production.

Figure 64. Synchronous non-multiplexed PSRAM write timings**Table 79. Synchronous non-multiplexed PSRAM write timings⁽¹⁾⁽²⁾**

Symbol	Parameter	Min	Max	Unit
$t_w(CLK)$	FSMC_CLK period	$2T_{HCLK} - 1$	-	ns
$t_{d(CLKL-NExL)}$	FSMC_CLK low to FSMC_NEx low (x=0..2)	-	1	ns
$t_{d(CLKL-NExH)}$	FSMC_CLK low to FSMC_NEx high (x= 0...2)	1	-	ns

Figure 73. NAND controller waveforms for common memory read access**Figure 74. NAND controller waveforms for common memory write access****Table 82. Switching characteristics for NAND Flash read cycles⁽¹⁾⁽²⁾**

Symbol	Parameter	Min	Max	Unit
$t_{w(NOE)}$	FSMC_NOE low width	$4T_{HCLK} - 1$	$4T_{HCLK} + 2$	ns
$t_{su(D-NOE)}$	FSMC_D[15:0] valid data before FSMC_NOE high	9	-	ns
$t_{h(NOE-D)}$	FSMC_D[15:0] valid data after FSMC_NOE high	3	-	ns
$t_{d(ALE-NOE)}$	FSMC_ALE valid before FSMC_NOE low	-	$3T_{HCLK}$	ns
$t_{h(NOE-ALE)}$	FSMC_NWE high to FSMC_ALE invalid	$3T_{HCLK} + 2$	-	ns

1. $C_L = 30$ pF.

2. Guaranteed by characterization results, not tested in production.

Table 97. Document revision history (continued)

Date	Revision	Changes
13-Jul-2010	4 (continued)	Added USB OTG_FS features in Section 3.28: Universal serial bus on-the-go full-speed (OTG_FS). Updated V_{CAP_1} and V_{CAP_2} capacitor value to 2.2 µF in Figure 19: Power supply scheme. Removed DAC, modified ADC limitations, and updated I/O compensation for 1.8 to 2.1 V range in Table 15: Limitations depending on the operating power supply range. Added V_{BORL}, V_{BORM}, V_{BORH} and I_{RUSH} in Table 19: Embedded reset and power control block characteristics. Removed table Typical current consumption in Sleep mode with Flash memory in Deep power down mode. Merged typical and maximum current consumption sections and added Table 21: Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator disabled), Table 20: Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator enabled) or RAM, Table 22: Typical and maximum current consumption in Sleep mode, Table 23: Typical and maximum current consumptions in Stop mode, Table 24: Typical and maximum current consumptions in Standby mode, and Table 25: Typical and maximum current consumptions in VBAT mode. Update Table 34: Main PLL characteristics and added Section 6.3.11: PLL spread spectrum clock generation (SSCG) characteristics. Added Note 8 for CIO in Table 48: I/O AC characteristics. Updated Section 6.3.18: TIM timer characteristics. Added T_{NRST_OUT} in Table 49: NRST pin characteristics. Updated Table 52: I2C characteristics. Removed 8-bit data in and data out waveforms from Figure 48: ULPI timing diagram. Removed note related to ADC calibration in Table 67. Section 6.3.20: 12-bit ADC characteristics: ADC characteristics tables merged into one single table; tables ADC conversion time and ADC accuracy removed. Updated Table 68: DAC characteristics. Updated Section 6.3.22: Temperature sensor characteristics and Section 6.3.23: VBAT monitoring characteristics. Update Section 6.3.26: Camera interface (DCMI) timing specifications. Added Section 6.3.27: SD/SDIO MMC card host interface (SDIO) characteristics, and Section 6.3.28: RTC characteristics. Added Section 7.7: Thermal characteristics. Updated Table 91: LQFP176 - Low profile quad flat package 24 × 24 × 1.4 mm package mechanical data and Figure 86: LQFP176 - Low profile quad flat package 24 × 24 × 1.4 mm, package outline. Changed tape and reel code to TX in Table 96: Ordering information scheme. Added Table 101: Main applications versus package for STM32F2xxx microcontrollers. Updated figures in Appendix A.2: USB OTG full speed (FS) interface solutions and A.3: USB OTG high speed (HS) interface solutions. Updated Figure 94: Audio player solution using PLL, PLLI2S, USB and 1 crystal and Figure 95: Audio PLL (PLLI2S) providing accurate I2S clock.

Table 97. Document revision history (continued)

Date	Revision	Changes
22-Apr-2011	6 (continued)	Updated <i>Typical and maximum current consumption</i> conditions, as well as <i>Table 21: Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator disabled)</i> and <i>Table 20: Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator enabled) or RAM</i>. Added <i>Figure 23</i>, <i>Figure 24</i>, <i>Figure 25</i>, and <i>Figure 26</i>. Updated <i>Table 22: Typical and maximum current consumption in Sleep mode</i>, and added <i>Figure 27</i> and <i>Figure 28</i>. Updated <i>Table 23: Typical and maximum current consumptions in Stop mode</i>. Added <i>Figure 29: Typical current consumption vs. temperature in Stop mode</i>. Updated <i>Table 24: Typical and maximum current consumptions in Standby mode</i> and <i>Table 25: Typical and maximum current consumptions in VBAT mode</i>. Updated <i>On-chip peripheral current consumption</i> conditions and <i>Table 26: Peripheral current consumption</i>. Updated $t_{WUSTDBY}$ and t_{WUSTOP} and added <i>Note 3</i> in <i>Table 27: Low-power mode wakeup timings</i>. Maximum f_{HSE_ext} and minimum $t_{w(HSE)}$ values updated in <i>Table 28: High-speed external user clock characteristics</i>. Updated C and g_m in <i>Table 30: HSE 4-26 MHz oscillator characteristics</i>. Updated R_F, I_2, g_m, and $t_{su(LSE)}$ in <i>Table 31: LSE oscillator characteristics (fLSE = 32.768 kHz)</i>. Added <i>Note 1</i> and updated ACC_{HSI}, $IDD_{(HSI)}$, and $t_{su(HSI)}$ in <i>Table 32: HSI oscillator characteristics</i>. Added <i>Figure 34: ACCHSI versus temperature</i>. Updated f_{LSI}, $t_{su(LSI)}$ and $IDD_{(LSI)}$ in <i>Table 33: LSI oscillator characteristics</i>. Added <i>Figure 35: ACCLSI versus temperature</i>. <i>Table 34: Main PLL characteristics</i>: removed note 1, updated t_{LOCK}, jitter, $IDD_{(PLL)}$ and $IDD_{A(PLL)}$, added <i>Note 2</i> for f_{PLL_IN} minimum and maximum values. <i>Table 35: PLLI2S (audio PLL) characteristics</i>: removed note 1, updated t_{LOCK}, jitter, $IDD_{(PLLI2S)}$ and $IDD_{A(PLLI2S)}$, added <i>Note 2</i> for f_{PLLI2S_IN} minimum and maximum values. Added <i>Note 1</i> in <i>Table 36: SSCG parameters constraint</i>. Updated <i>Table 37: Flash memory characteristics</i>. Modified <i>Table 38: Flash memory programming</i> and added <i>Note 2</i> for t_{prog}. Updated t_{prog} and added <i>Note 1</i> in <i>Table 39: Flash memory programming with VPP</i>. Modified <i>Figure 40: Recommended NRST pin protection</i>. Updated <i>Table 42: EMI characteristics</i> and EMI monitoring conditions in <i>Section : Electromagnetic Interference (EMI)</i>. Added <i>Note 2</i> related to $V_{ESD(HBM)}$ in <i>Table 43: ESD absolute maximum ratings</i>. Updated <i>Table 48: I/O AC characteristics</i>. Added <i>Section 6.3.15: I/O current injection characteristics</i>. Modified maximum frequency values and conditions in <i>Table 48: I/O AC characteristics</i>. Updated $t_{res(TIM)}$ in <i>Table 50: Characteristics of TIMx connected to the APB1 domain</i>. Modified $t_{res(TIM)}$ and f_{EXT} <i>Table 51: Characteristics of TIMx connected to the APB2 domain</i>.

Table 97. Document revision history (continued)

Date	Revision	Changes
20-Dec-2011	8 (continued)	Added maximum power consumption at $T_A=25\text{ }^{\circ}\text{C}$ in Table 23: Typical and maximum current consumptions in Stop mode. Updated md minimum value in Table 36: SSCG parameters constraint. Added examples in Section 6.3.11: PLL spread spectrum clock generation (SSCG) characteristics. Updated Table 54: SPI characteristics and Table 55: I2S characteristics. Updated Figure 48: ULPI timing diagram and Table 61: ULPI timing. Updated Table 63: Dynamics characteristics: Ethernet MAC signals for SMI, Table 64: Dynamics characteristics: Ethernet MAC signals for RMII, and Table 65: Dynamics characteristics: Ethernet MAC signals for MII. Section 6.3.25: FSMC characteristics: updated Table 72 to Table 83, changed C_L value to 30 pF, and modified FSMC configuration for asynchronous timings and waveforms. Updated Figure 62: Synchronous multiplexed PSRAM write timings. Updated Table 84: DCMI characteristics. Updated Table 92: UFBGA176+25 - ultra thin fine pitch ball grid array 10 × 10 × 0.6 mm mechanical data. Updated Table 96: Ordering information scheme. Appendix A.2: USB OTG full speed (FS) interface solutions: updated Figure 87: USB OTG FS (full speed) host-only connection and added Note 2, updated Figure 88: OTG FS (full speed) connection dual-role with internal PHY and added Note 3 and Note 4, modified Figure 89: OTG HS (high speed) device connection, host and dual-role in high-speed mode with external PHY and added Note 2. Appendix A.3: USB OTG high speed (HS) interface solutions: removed figures USB OTG HS device-only connection in FS mode and USB OTG HS host-only connection in FS mode, updated Figure 89: OTG HS (high speed) device connection, host and dual-role in high-speed mode with external PHY. Added Appendix A.4: Ethernet interface solutions. Updated disclaimer on last page.
24-Apr-2012	9	Updated V_{DD} minimum value in Section 2: Description. Updated number of USB OTG HS and FS, modified packages for STM32F2071x part numbers, added Note 1 related to FSMC and Note 2 related to SPI/I2S, and updated Note 3 in Table 2: STM32F205xx features and peripheral counts and Table 3: STM32F207xx features and peripheral counts. Added Note 2 and update TIM5 in Figure 4: STM32F20x block diagram. Updated maximum number of maskable interrupts in Section 3.10: Nested vectored interrupt controller (NVIC). Updated V_{DD} minimum value in Section 3.14: Power supply schemes. Updated Note a in Section 3.16.1: Regulator ON. Removed STM32F205xx in Section 3.28: Universal serial bus on-the-go full-speed (OTG_FS).